

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE                  STATEMENT BY APPLICANT(S)</b>	<b>Complete if Known</b>	
	Application Number	Unknown
	Filing Date	Herewith
	First Named Inventor	D'Evelyn
	Art Unit	Unknown
Examiner Name	Unknown	
Sheet 1 of 3	Attorney Docket No.	132852-1/GCRZ 2 00025

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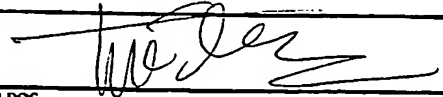
Examiner Initials*	Cite No.	Document No. Number-Kind Code (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
TT	AA	US-5,578,839	11-26-1996	Nakamura et al.	
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TT	AL	US-6,031,858	02-29-2000	Hatakoshi et al.	

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TT	AM	PCT - WO 01/37351 A1	05-25-2001	Cree Lighting Co.		<input type="checkbox"/>
TT	AN	PCT - WO 01/24285 A1	04-05-2001	Lumileds Lighting U.S. LLC		<input type="checkbox"/>
	AO					<input type="checkbox"/>
	AP					<input type="checkbox"/>

**OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
TT	AQ	KAMP et al., GaN Homoepitaxy for Device Applications, Kamp et al., MRS Internet J. Nitride Semicond. Res. 4SI, G10.2 (1999)	<input type="checkbox"/>
TT	AR	FINI et al. <i>In situ</i> , Real-Time Measurement of Wing Tilt During Lateral Epitaxial Overgrowth of GaN; Applied Physics Letters, Volume 76, Number 26, June 26, 2000	<input type="checkbox"/>
TT	AS	PELZMANN et al., Blue Light-Emitting Diodes on GaN Substrates, Growth and Characterization, Journal of Crystal Growth 189/190 (1998) 167-171	<input type="checkbox"/>
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TT	AV	KUAN et al., Dislocation Mechanisms in the GaN Lateral Overgrowth by Hydride Vapor Phase Epitaxy	<input type="checkbox"/>

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TT	BA	US-6,100,586	08-08-2000	Chen et al.	
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TT	BQ	SAKAI et al., Transmission Electron Microscopy of Defects in GaN Films Formed by Epitaxial Lateral Overgrowth, Applied Physics Letters, Volume 73, Number 4, July 27, 1998	<input type="checkbox"/>
TT	BR	MARCHAND et al., Microstructure of GaN Laterally Overgrown by Metalorganic Chemical Vapor Deposition, Applied Physics Letters, Volume 73, Number 6, August 10, 1998	<input type="checkbox"/>
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TT	BT	Patent Abstract of Japan, Publication No. 2000-022212, Date 21.01.2000	<input type="checkbox"/>
TT	BU	D'EVELYN et al., Homoepitaxial Gallium-Nitride-Based Light Emitting Device and Method for Producing, U.S. Application Serial No. 09/694,690; Filed October 23, 2000	<input type="checkbox"/>
TT	BV	D'EVELYN et al., Gallium Nitride Crystal and Method of Making Same; U.S. Application Serial No. 10/329,981	<input type="checkbox"/>

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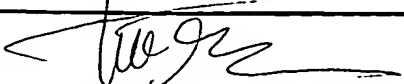
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	CG				
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	CJ				
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